

Silicon PNP Power Transistors

2SB1657

DESCRIPTION

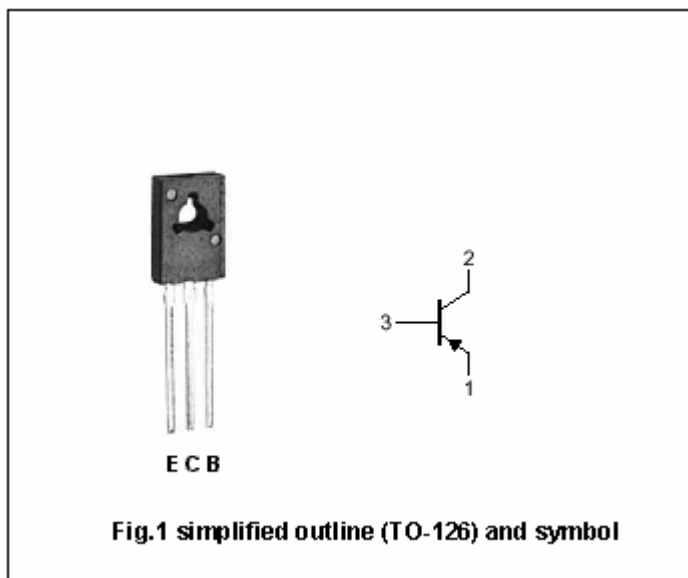
- With TO-126 package
- Low collector saturation voltage
- High DC current gain

APPLICATIONS

- For audio frequency amplifier and switching applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-30	V
V _{CEO}	Collector-emitter voltage	Open base	-30	V
V _{EBO}	Emitter-base voltage	Open collector	-6	V
I _C	Collector current (DC)		-5	A
I _{CM}	Collector current-Peak		-8	A
I _B	Base current (DC)		-1	A
P _T	Total power dissipation	T _a =25°C	0.1	W
		T _C =25°C	10	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA ; I _B =0	-30			V
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =-0.5A; I _B =-25mA			-0.15	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =-1A; I _B =-50mA			-0.25	V
V _{CEsat-3}	Collector-emitter saturation voltage	I _C =-2A; I _B =-100mA			-0.40	V
V _{CEsat-4}	Collector-emitter saturation voltage	I _C =-3A; I _B =-75mA			-1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-1A; I _B =-50mA			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-30V; I _E =0			-0.1	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-6V; I _C =0			-0.1	μA
h _{FE-1}	DC current gain	I _C =-0.5A ; V _{CE} =-2V	150		600	
h _{FE-2}	DC current gain	I _C =-3A ; V _{CE} =-2V	70			
f _T	Transition frequency	I _C =-50mA ; V _{CE} =-10V		75		MHz
C _{OB}	Collector output capacitance	I _E =0;f=1MHz ; V _{CB} =-10V		60		pF

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PACKAGE OUTLINE

